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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known		
				Application Number	09/837,558	
Sheet		1	of	1	Filing Date	April 19, 2001
					First Named Inventor	Shunpei Yamazaki
					Art Unit	2814
					Examiner Name	N. Ngo
					Attorney Docket Number	740756-2297

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
MO NA		US-5,702,963	12-30-1997	Vu et al.	
		US-6,225,150 B1	05-01-2001	Lee et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	Nathan W. Ftg	Date Considered	8/7/03
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Form PTO-1449
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Patent and Trademark Office

Atty Docket 0756-2

Serial No. 09/837,558

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: April 19, 2001

Group Art Unit:
Unassigned

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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<i>NA</i>	4,748,485	05/31/1988	Vasudev			
<i>NA</i>	4,977,105	12/11/1990	Okamoto et al.			
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<i>NA</i>	4,996,575	02/26/1991	Ipri et al.			
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Unassigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	6,252,248 B1	06/26/2001	Sano et al.			

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Unassigned

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Nathan Ohtani

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